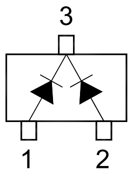
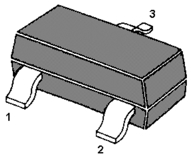
MMBD6100

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance





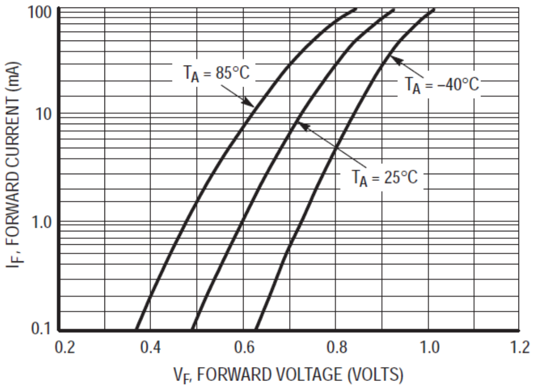
Marking Code: **A4**
TO-236 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

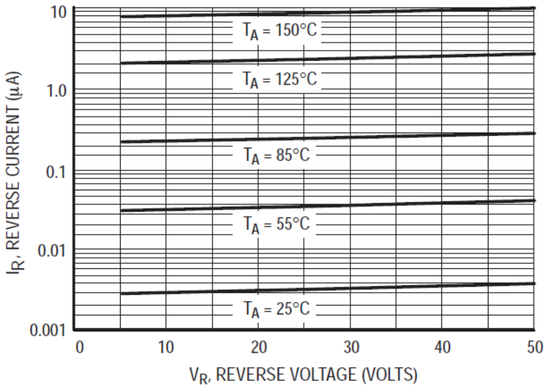
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s at t = 1 µs	I_{FSM}	1 2	A
Power Dissipation	P_{tot}	300	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

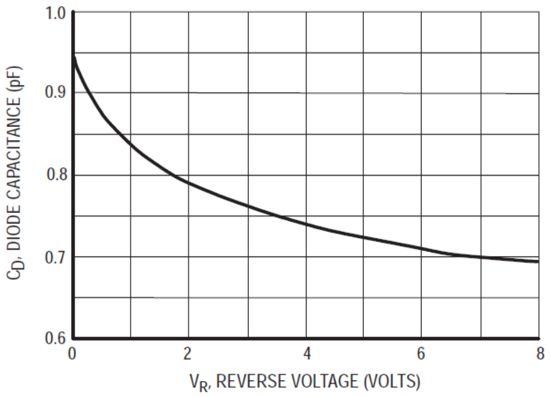
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 100 mA	V_F	0.55 0.85	0.7 1.1	V
Reverse Current at V_R = 50 V	I_R	-	0.1	µA
Reverse Breakdown Voltage at I_R = 100 µA	$V_{(BR)R}$	70	-	V
Total Capacitance at V_R = 0	C_T	-	2.5	pF
Reverse Recovery Time at I_F = I_R = 10 mA	t_{rr}	-	4	ns



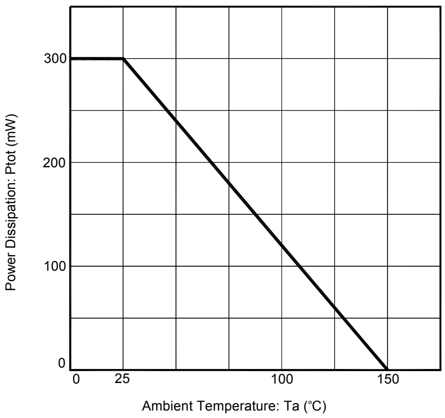
Forward Voltage



Leakage Current



Capacitance



Derating Curve